

**AMENDMENTS TO THE SPECIFICATION**

**Before the first paragraph of page 1, please insert the following paragraph:**

- - This application claims priority of Korean application no. 41409/2003, filed June 25, 2003, and is the national stage application of PCT/KR2004/001480, filed June 21, 2004. - -

**Please amend the paragraph starting at page 2, line 37 as follows:**

According to an aspect of the invention for realizing the above objects, there is provided [[A]] a nitride based 3-5 group compound semiconductor Light emitting device comprising: a substrate; a buffer layer formed above the substrate; a first In-doped GaN layer formed above the buffer layer; an  $\text{In}_x\text{Ga}_{1-x}\text{N}/\text{In}_y\text{Ga}_{1-y}\text{N}$  super lattice structure layer formed above the first In-doped GaN layer; a first electrode contact layer formed above the  $\text{In}_x\text{Ga}_{1-x}\text{N}/\text{In}_y\text{Ga}_{1-y}\text{N}$  super lattice structure layer; an active layer formed above the first electrode contact layer and functioning to emit light; a second In-doped GaN layer; a GaN layer formed above the second In-doped GaN layer; and a second electrode contact layer formed above the GaN layer.

**Please amend the paragraph starting at page 3, line 13 as follows:**

According to another aspect of the invention for realizing the above objects, there is provided [[A]] a nitride based 3-5 group compound

semiconductor light emitting device comprising: a substrate; a buffer layer formed above the substrate; a first In-doped GaN layer formed above the buffer layer; a first electrode contact layer formed above the first In-doped GaN layer; an active layer formed above the first electrode contact layer and functioning to emit light; a GaN layer formed above the active layer; and a second electrode contact layer formed above the GaN layer.

**Please amend the paragraph starting at page 3, line 23 as follows:**

According to further an aspect of the invention for realizing the above objects, there is provided [[A]] a nitride based 3-5 group compound semiconductor light emitting device comprising: a substrate; a buffer layer formed above the substrate; a first electrode contact layer formed above the GaN buffer layer; an active layer formed above the first electrode contact layer, and including a low mole In-doped  $\text{In}_x\text{Ga}_{1-x}\text{N}$  layer, an  $\text{In}_y\text{Ga}_{1-y}\text{N}$  well layer and an  $\text{In}_z\text{Ga}_{1-z}\text{N}$  barrier layer; a GaN layer formed above the active layer; and a second electrode contact layer formed above the GaN layer.

**Please amend the paragraph starting at page 3, line 33 as follows:**

According to still another aspect of the invention for realizing the above objects, there is provided [[A]] a fabrication method of a nitride based 3-5 group compound semiconductor light emitting device, comprising: forming a buffer layer above a substrate; forming a first In-doped GaN layer above the buffer layer; forming a first electrode contact layer above the first In-doped GaN layer;

forming an active layer for emitting light above the first electrode contact layer;  
forming a GaN layer above the active layer; and forming a second electrode  
contact layer above the GaN layer.